



Phase Control Thyristor

DS6164-1 December 2014 (LN32187)

FEATURES

- Double Side Cooling
- High Surge Capability

KEY PARAMETERS

V _{DRM}	4200V
I _{T(AV)}	6138A
I _{TSM}	90910A
dV/dt*	2000V/µs
dl/dt	200A/µs

* Higher dV/dt selections available

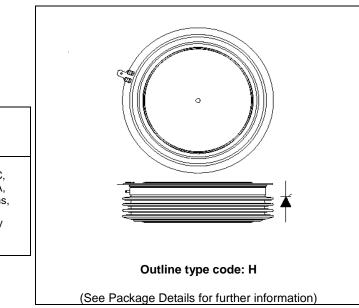


Fig. 1 Package outline

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR6140H42 DCR6140H40 DCR6140H38	4200 4000 3800	$\begin{array}{l} T_{vj} = -40^{\circ}C \ to \ 125^{\circ}C, \\ I_{DRM} = I_{RRM} = 600 \text{mA}, \\ V_{DRM}, \ V_{RRM} \ t_p = 10 \text{ms}, \\ V_{DSM} \& \ V_{RSM} = \\ V_{DRM} \& \ V_{RRM} + 100 V \\ respectively \end{array}$

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR6140H42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.



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CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Sid	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	6138	А
I _{T(RMS)}	RMS value	-	9642	А
Ι _Τ	Continuous (direct) on-state current	-	8409	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$	90.91	kA
l ² t	I ² t for fusing	$V_R = 0$	41.32	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	S	Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.004255	°C/W
		Single side cooled	Anode DC	-	0.008	°C/W
			Cathode DC	-	0.0093	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 135.0kN	Double side	-	0.0009	°C/W
		(with mounting compound)	Single side	-	0.0018	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / V _{RRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
F _m	Clamping force			120	155	kN

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DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	ns	Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	600	mA
dV/dt	Max. linear rate of rise of off-state voltage	То 67% V _{DRM} , Т _ј = 125°С, ga	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% V_{DRM} to 2x $I_{\text{T(AV)}}$	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω ,	Non-repetitive	-	500	A/µs
		t _r < 0.5µs, T _j = 125°C				
V _{T(TO)}	Threshold voltage – Low level	500 to 4000A at T _{case} = 125°	С	-	0.860	V
	Threshold voltage – High level	4000 to 8000A at T _{case} = 125	°C	-	1.090	V
rΤ	On-state slope resistance – Low level	500A to 4000A at $T_{case} = 125$	5°C	-	0.14	mΩ
	On-state slope resistance – High level	4000A to 8000A at T _{case} = 125°C		-	0.085	mΩ
t _{gd}	Delay time	V _D = 67% V _{DRM} , gate source	30V, 10Ω	-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$I_T = 3000A, T_j = 125^{\circ}C,$ $V_R = 200V, dI/dt = 1A/\mu s,$			700	μs
		$dV_{DR}/dt = 20V/\mu s linear$				
Qs	Stored charge	I⊤ = 3000A, Ti = 125°C, dl/dt	- 1 A/us	1500	3800	μC
I _{RR}	Reverse recovery current	V _{Rpeak} ~2520V, V _R ~ 1680V	πτρο,	32	49	A
۱L	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 5V$		-	3	A
I _H	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 50^{\circ}$	0A, I _T = 5A	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

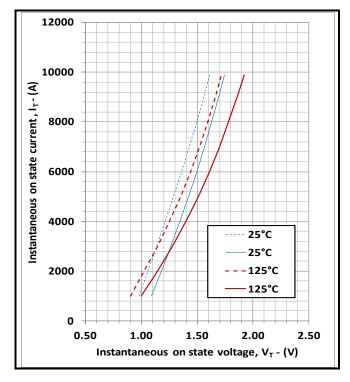


Fig.2 Maximum & minimum on-state characteristics

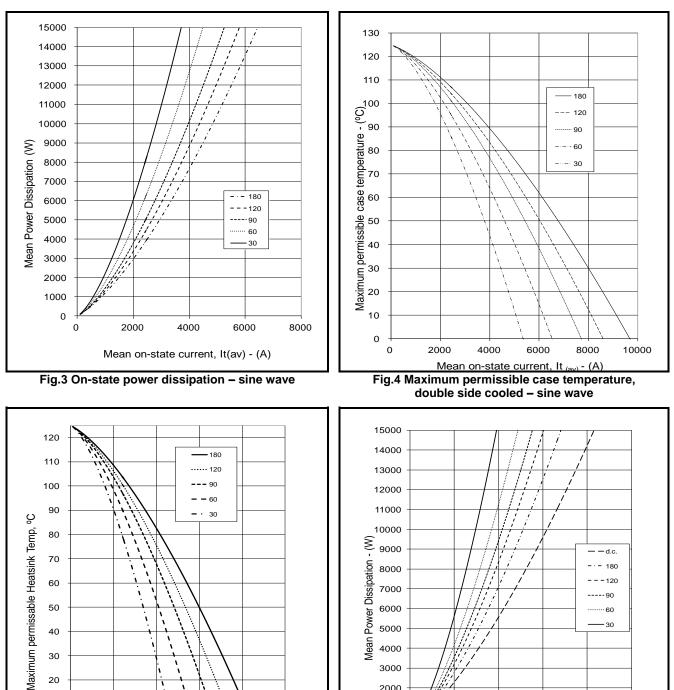
V_{TM} EQUATION

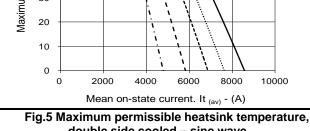
 $V_{TM} = A + BIn (I_T) + C.I_T + D.\sqrt{I_T}$

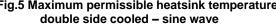
Where A = 1.27876 B = -0.12239 C = 0 D = 0.01793 these values are valid for T_j = 125°C for I_T 500A to 8000A

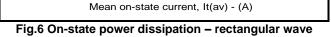


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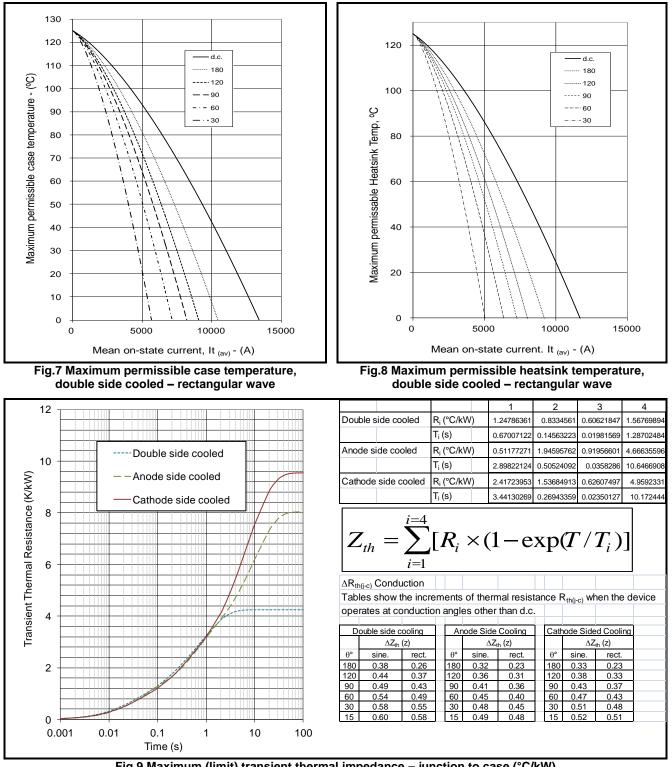


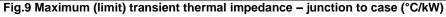


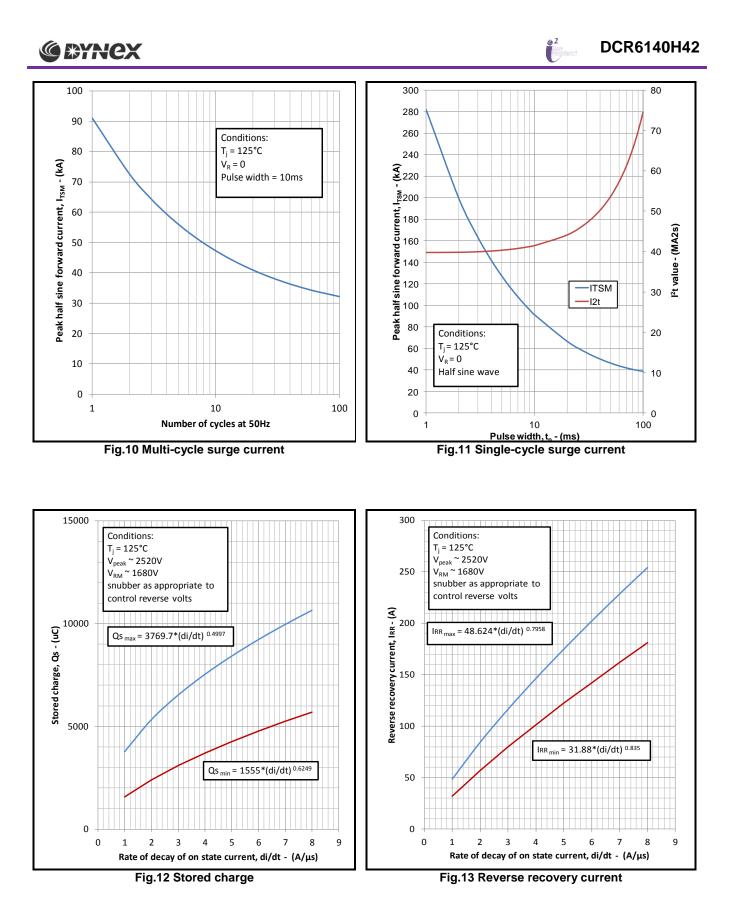




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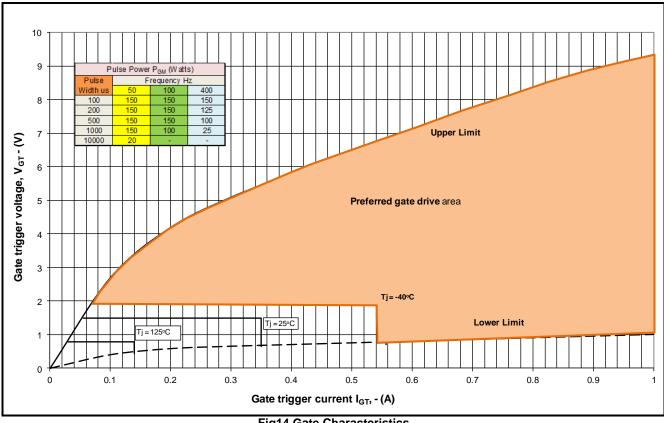
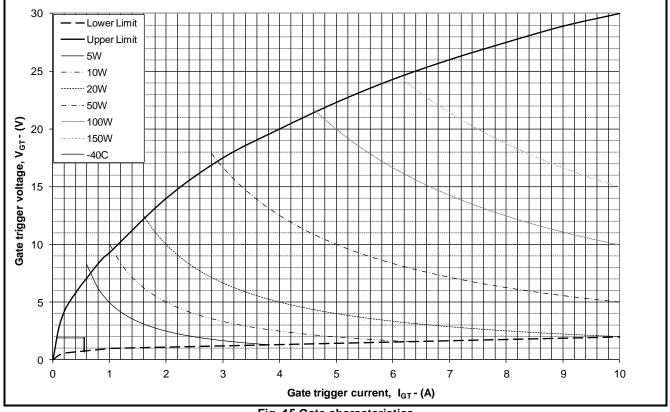


Fig14 Gate Characteristics



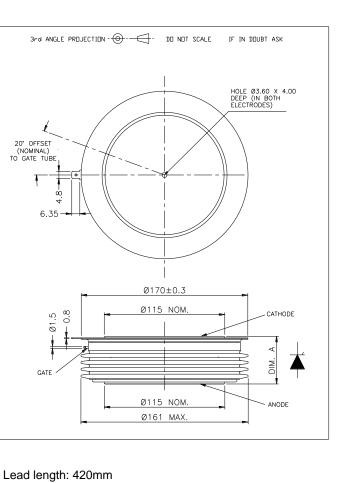


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PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

	Maximum	Minimum
	Thickness	Thickness
Device	(mm)	(mm)
DCR6140H42	35.15	34.28
DCR6650H42	35.15	34.28
DCR5240H52	35.27	34.4
DCR5890H52	35.27	34.4
DCR4420H65	35.3	34.7
DCR4660H65	35.3	34.7
DCR3640H85	35.65	35.05
DCR3980H85	35.65	35.05



Lead terminal connector: M4 ring

Package outline type code:H

Fig.16 Package outline



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